

<b>Electronic Patent Application Fee Transmittal</b>				
<b>Application Number:</b>	10585744			
<b>Filing Date:</b>	12-Jul-2006			
<b>Title of Invention:</b>	N-TYPE GROUP III NITRIDE SEMICONDUCTOR LAYERED STRUCTURE			
<b>First Named Inventor/Applicant Name:</b>	Akira Bandoh			
<b>Filer:</b>	Abraham Jacob Rosner/Sharon Jones			
<b>Attorney Docket Number:</b>	Q81505			
Filed as Large Entity				
<b>U.S. National Stage under 35 USC 371 Filing Fees</b>				
Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
<b>Basic Filing:</b>				
<b>Pages:</b>				
<b>Claims:</b>				
<b>Miscellaneous-Filing:</b>				
<b>Petition:</b>				
<b>Patent-Appeals-and-Interference:</b>				
<b>Post-Allowance-and-Post-Issuance:</b>				
<b>Extension-of-Time:</b>				

Description	Fee Code	Quantity	Amount	Sub-Total in USD(\$)
<b>Miscellaneous:</b>				
Submission- Information Disclosure Stmt	1806	1	180	180
<b>Total in USD (\$)</b>				<b>180</b>